

LME49723

Dual High Fidelity Audio Operational Amplifier

General Description

The LME49723 is part of the ultra-low distortion, low noise, high slew rate operational amplifier series optimized and fully specified for high performance, high fidelity applications. Combining advanced leading-edge process technology with state-of-the-art circuit design, the LME49723 audio operational amplifiers deliver superior audio signal amplification for outstanding audio performance. The LME49723 combines extremely low voltage noise density $(3.6\text{nV}/\sqrt{\text{Hz}})$ with vanishingly low THD+N (0.0002%) to easily satisfy the most demanding audio applications. To ensure that the most challenging loads are driven without compromise, the LME49723 has a high slew rate of $\pm 20\text{V}/\mu\text{s}$ and an output current capability of $\pm 26\text{mA}$. Further, dynamic range is maximized by an output stage that drives $2k\Omega$ loads to within 1V of either power supply voltage and to within 1.4V when driving 600Ω loads.

The LME49723's outstanding CMRR (100dB), PSRR (100dB), and V_{OS} (0.3mV) give the amplifier excellent operational amplifier DC performance.

The LME49723 has a wide supply range of $\pm 2.5 \text{V}$ to $\pm 17 \text{V}$. Over this supply range the LME49723's input circuitry maintains excellent common-mode and power supply rejection, as well as maintaining its low input bias current. The LME49723 is unity gain stable.

The LME49723 is available in an 8-lead narrow body SOIC. Demonstration boards are available for each package.

Key Specifications

■ Power Supply Voltage Range ±2.5V to ±17V

■ THD+N (A...= 1 V ...

THD+N ($A_V = 1$, $V_{OUT} = 3V_{RMS}$, $f_{IN} = 1kHz$)

 $R_{L} = 2k\Omega \qquad 0.0002\% \text{ (typ)}$

$R_L = 600\Omega$	0.0002% (typ)
■ Input Noise Density	3.6nV/ $\sqrt{\text{Hz}}$ (typ)
■ Slew Rate	±8V/μs (typ)
■ Gain Bandwidth Product	17MHz (typ)
■ Open Loop Gain (R _L = 600Ω)	105dB (typ)
■ Input Bias Current	200nA (typ)
■ Input Offset Voltage	0.3mV (typ)

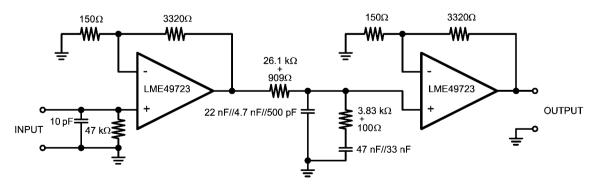
Features

- Easily drives 600Ω loads
- Optimized for superior audio signal fidelity
- Output short circuit protection
- PSRR and CMRR exceed 100dB (typ)
- SOIC package

Applications

- High quality audio amplification
- High fidelity preamplifiers
- High fidelity multimedia
- Phono pre amps
- High performance professional audio
- High fidelity equalization and crossover networks
- High performance line drivers
- High performance line receivers
- High fidelity active filters

Typical Application

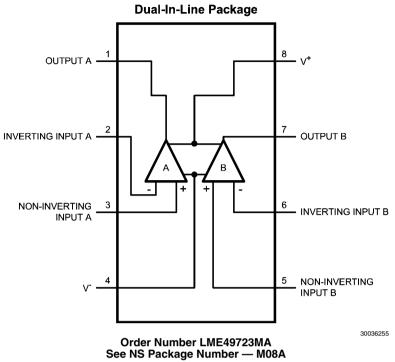


Note: 1% metal film resistors, 5% polypropylene capacitors

Passively Equalized RIAA Phono Preamplifier

300362k5

Connection Diagram



Absolute Maximum Ratings (Notes 1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Power Supply Voltage $(V_S = V^+ - V^-)$ 36V

Storage Temperature -65°C to 150°C

Input Voltage (V-) - 0.7V to (V+) + 0.7V

Output Short Circuit (Note 3) Continuous Power Dissipation Internally Limited ESD Susceptibility (Note 4) 800V ESD Susceptibility (Note 5) 180V Junction Temperature 150°C Thermal Resistance

 θ_{IA} (SO) 145°C/W

Temperature Range

 $-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le 85^{\circ}\text{C}$ $T_{MIN} \le T_A \le T_{MAX}$ Supply Voltage Range $\pm 2.5 \text{V} \le \text{V}_{\text{S}} \le \pm 17 \text{V}$

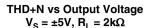
Electrical Characteristics for the LME49723 (Notes 1, 2) The specifications apply for $V_S = \pm 7V$, $\rm R_L = 2k\Omega,\, f_{\rm IN} = 1kHz,\, T_A = 25^{\circ}C,\, unless$ otherwise specified.

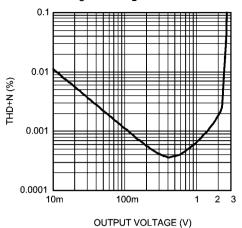
	Parameter	Conditions	LME49723		
Symbol			Typical	Limit	Units (Limits)
			(Note 6)	(Note 7)	
THD+N	Total Harmonic Distortion + Noise	$A_{V} = 1, V_{OUT} = 3V_{rms}$ $R_{L} = 2k\Omega$ $R_{L} = 600\Omega$	0.0002 0.0002	0.0004	% (max)
IMD	Intermodulation Distortion	A _V = 1, V _{OUT} = 3V _{RMS} Two-tone, 60Hz & 7kHz 4:1	0.0005		%
GBWP	Gain Bandwidth Product		19	15	MHz (min)
SR	Slew Rate		±8	±6	V/µs (min)
FPBW	Full Power Bandwidth	V _{OUT} = 1V _{P-P} , –3dB referenced to output magnitude at f = 1kHz	4		MHz
	Equivalent Input Noise Voltage	f _{BW} = 20Hz to 20kHz	0.45	0.65	μV _{RMS} (max)
e _n	Equivalent Input Noise Density	f = 1kHz f = 10Hz	3.2 8.5	5	nV/√ Hz (max)
i _n	Current Noise Density	f = 1kHz f = 10Hz	0.7 1.3		pAJ√Hz
V _{os}	Offset Voltage		±0.3	1	mV (max)
ΔV _{OS} /ΔTemp	Average Input Offset Voltage Drift vs Temperature	–40°C ≤ T _A ≤ 85°C	0.2		μV/°C
PSRR	Average Input Offset Voltage Shift vs Power Supply Voltage	ΔV _S = 20V (Note 8)	100	95	dB (min)
ISO _{CH-CH}	Channel-to-Channel Isolation	$f_{IN} = 1kHz$ $f_{IN} = 20kHz$	118 112		dB
I _B	Input Bias Current	$V_{CM} = 0V$	200	300	nA (max)
ΔI _{OS} /ΔTemp	Input Bias Current Drift vs Temperature	–40°C ≤ T _A ≤ 85°C	0.1		nA/°C
I _{os}	Input Offset Current	V _{CM} = 0V	7	100	nA (max)
V _{IN-CM}	Common-Mode Input Voltage Range		±14	(V+) - 2.0 (V-) + 2.0	V (min)
CMRR	Common-Mode Rejection	-10V <vcm<10v< td=""><td>100</td><td>90</td><td>dB (min)</td></vcm<10v<>	100	90	dB (min)
	Differential Input Impedance		30		kΩ
Z _{IN}	Common Mode Input Impedance	-10V <vcm<10v< td=""><td>1000</td><td></td><td>ΜΩ</td></vcm<10v<>	1000		ΜΩ
	Open Loop Voltage Gain	$-10V$ <vout<10v, r<sub="">L = 600Ω</vout<10v,>	100	98	
A _{VOL}		$-10V$ <vout<10v, r<sub="">L = $2k\Omega$</vout<10v,>	105		dB (min)
		$-10V$ <vout<10v, r<sub="">L = 10kΩ</vout<10v,>	105		

			LME49723		
Symbol	Parameter	Conditions	Typical	Limit	Units
I			(Note 6)	(Note 7)	(Limits)
V _{OUTMAX}	Maximum Output Voltage Swing	$R_L = 600\Omega$	±13.5	±12.5	V (min)
		$R_L = 2k\Omega$	±14.0		
		$R_L = 10k\Omega$	±14.1		
I _{OUT}	Output Current	$R_L = 600\Omega, V_S = \pm 17V$	±25	±21	mA (min)
I _{OUT-CC}	Instantaneous Short Circuit Current		+53 -42		mA
R _{OUT}	Output Impedance	f _{IN} = 10kHz Closed-Loop Open-Loop	0.01 13		Ω
C _{LOAD}	Capacitive Load Drive Overshoot	100pF	16		%
I _s	Total Quiescent Current	I _{OUT} = 0mA	6.7	7.5	mA (max)

- Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur.
- **Note 2:** Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.
- Note 3: Amplifier output connected to GND, any number of amplifiers within a package.
- Note 4: Human body model, 100pF discharged through a 1.5k Ω resistor.
- Note 5: Machine Model ESD test is covered by specification EIAJ IC-121-1981. A 200pF cap is charged to the specified voltage and then discharged directly into the IC with no external series resistor (resistance of discharge path must be under 50Ω).
- Note 6: Typical specifications are specified at +25°C and represent the most likely parametric norm.
- Note 7: Tested limits are guaranteed to National's AOQL (Average Outgoing Quality Level).
- Note 8: PSRR is measured as follows: V_{OS} is measured at two supply voltages, $\pm 5V$ and $\pm 15V$. PSRR = | $20log(\Delta V_{OS}/\Delta V_S)$ |.

Typical Performance Characteristics



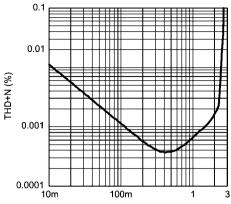


30036281

0.1

THD+N vs Output Voltage

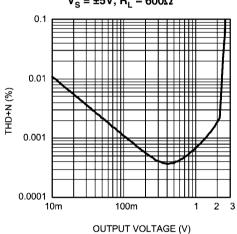
 $V_S = \pm 5V$, $R_I = 10k\Omega$



OUTPUT VOLTAGE (V)

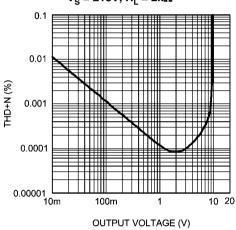
30036282

THD+N vs Output Voltage $V_S = \pm 5V, R_L = 600\Omega$



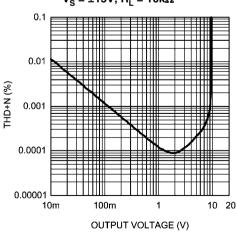
30036283

THD+N vs Output Voltage $V_S = \pm 15V, \dot{R}_L = 2k\Omega$



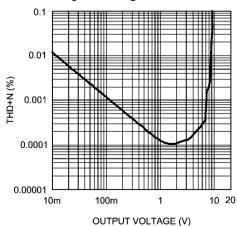
30036284

THD+N vs Output Voltage $V_S = \pm 15V$, $R_L = 10k\Omega$

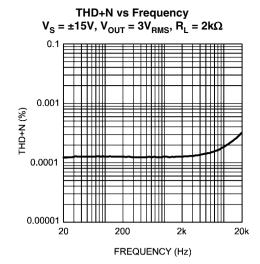


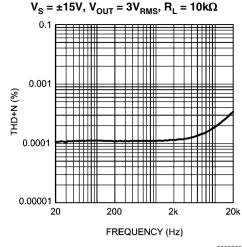
30036285

THD+N vs Output Voltage $V_{S} = \pm 15V, R_{L} = 600\Omega$



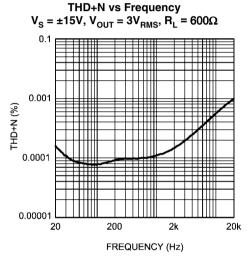
30036286



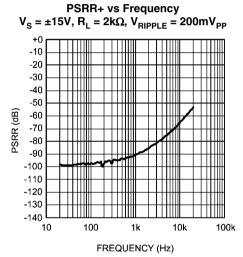


THD+N vs Frequency

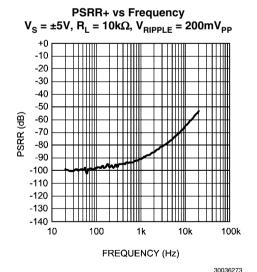
30036288



30036289

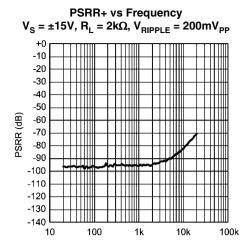


30036272



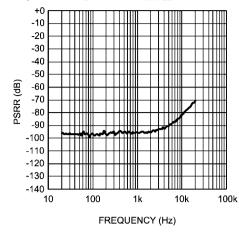
PSRR+ vs Frequency $V_S = \pm 5V$, $R_L = 600\Omega$, $V_{RIPPLE} = 200 \text{mV}_{PP}$ -20 -30 -40 -50 PSRR (dB) -60 -70 -80 -90 -100 -110 -120 -130 -140 10 10k 100k FREQUENCY (Hz)

30036274



FREQUENCY (Hz)

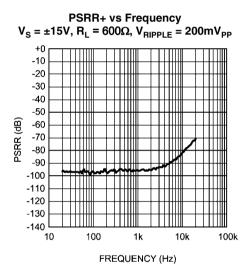
30036275



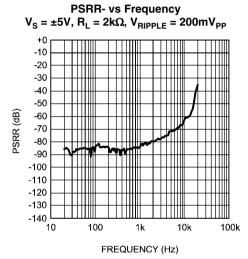
PSRR+ vs Frequency

 $V_S = \pm 15V$, $R_L = 10k\Omega$, $V_{RIPPLE} = 200mV_{PP}$

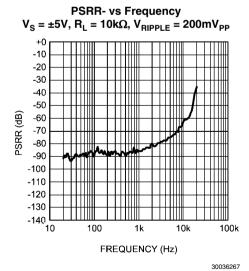
30036276



30036277



30036266

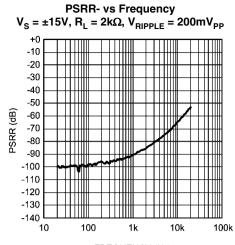


-10 -20 -30 -40 -50 -60 PSRR (dB) -70 -80 -90 -100 -110 -120 -130 -140 L 10 100k FREQUENCY (Hz)

PSRR- vs Frequency

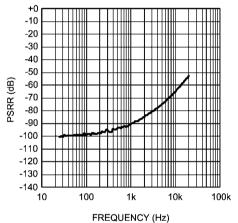
 $V_S = \pm 5V$, $R_L = 600\Omega$, $V_{RIPPLE} = 200 \text{mV}_{PP}$

30036268

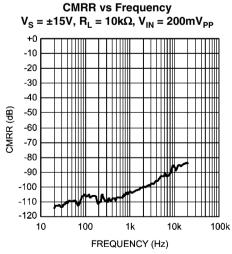


FREQUENCY (Hz) **PSRR- vs Frequency**

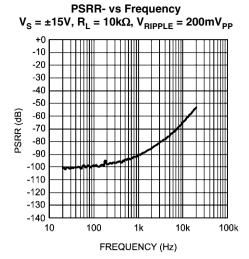
 $V_S = \pm 15V$, $R_L = 10k\Omega$, $V_{RIPPLE} = 200mV_{PP}$



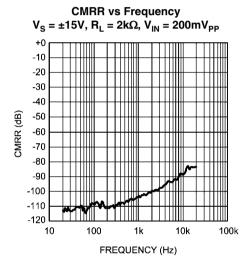
30036271



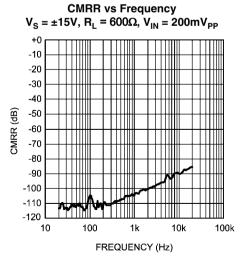
30036256



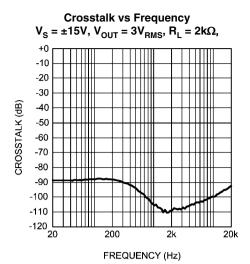
30036270



300362r4



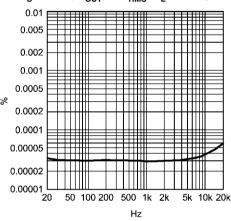
30036257



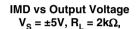
$V_S = \pm 15V$, $V_{OUT} = 3V_{RMS}$, $R_L = 10kΩ$, 0.01 0.005 0.0002 0.0001 0.00005 0.00002 0.00001 20 50 100 200 500 1k 2k 5k 10k 20k Hz

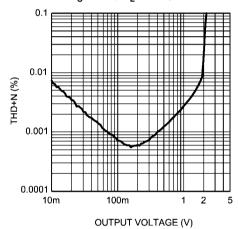
Crosstalk vs Frequency





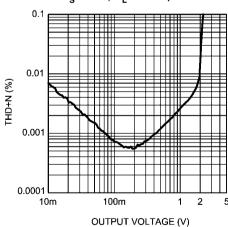
30036260





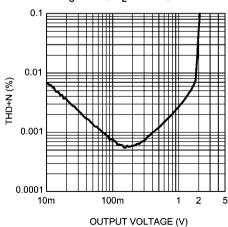
30036290

IMD vs Output Voltage $V_S = \pm 5V$, $R_L = 10k\Omega$,



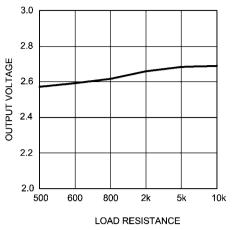
30036291

IMD vs Output Voltage $V_S = \pm 5V$, $R_L = 600\Omega$,



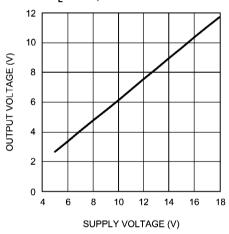
30036292

Output Voltage vs Load Resistance $V_S = \pm 5V$, THD+N = 1%



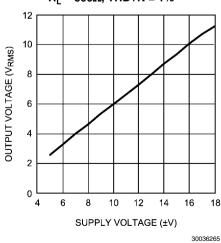
30036261

Output Voltage vs Supply Voltage $R_1 = 2k\Omega$, THD+N = 0.1%

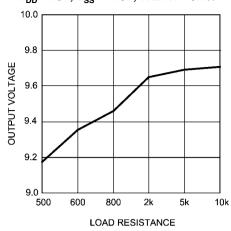


30036263

Output Voltage vs Supply Voltage $R_1 = 600\Omega$, THD+N = 1%

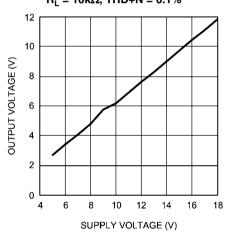


Output Voltage vs Load Resistance V_{DD} = 15V, V_{SS} = -15V, THD+N = 0.1%



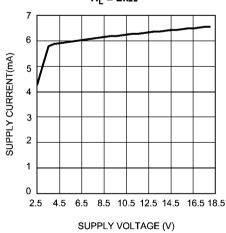
30036262

Output Voltage vs Supply Voltage $R_1 = 10k\Omega$, THD+N = 0.1%



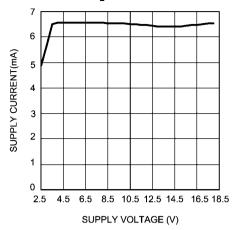
30036264

Supply Current vs Supply Voltage $R_L = 2k\Omega \label{eq:RL}$

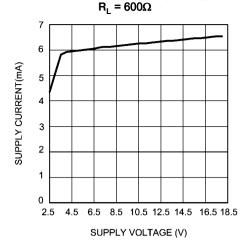


30036278

Supply Current vs Supply Voltage $R_L = 10k\Omega$



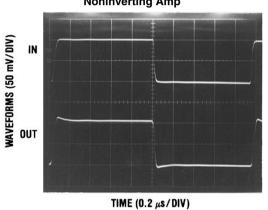
30036279



Supply Current vs Supply Voltage

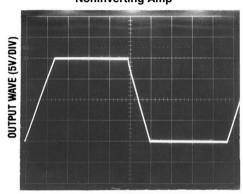
30036280

Noninverting Amp



30036224

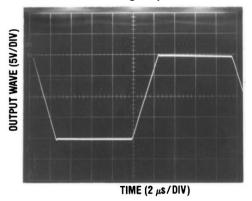
Noninverting Amp



TIME (2 µs/DIV)

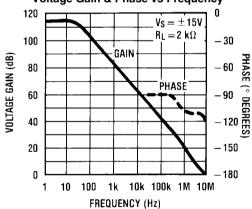
30036225

Inverting Amp

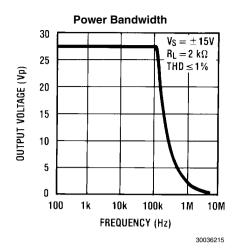


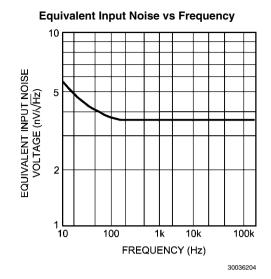
30036226

Voltage Gain & Phase vs Frequency



30036210





Application Information

DISTORTION MEASUREMENTS

The vanishingly low residual distortion produced by LME49723 is below the capabilities of all commercially available equipment. This makes distortion measurements just slightly more difficult than simply connecting a distortion meter to the amplifier's inputs and outputs. The solution, however, is quite simple: an additional resistor. Adding this resistor extends the resolution of the distortion measurement equipment.

The LME49723's low residual distortion is an input referred internal error. As shown in Figure 1, adding the 10Ω resistor connected between the amplifier's inverting and non-inverting

inputs changes the amplifier's noise gain. The result is that the error signal (distortion) is amplified by a factor of 101. Although the amplifier's closed-loop gain is unaltered, the feedback available to correct distortion errors is reduced by 101, which means that measurement resolution increases by 101. To ensure minimum effects on distortion measurements, keep the value of R1 low as shown in Figure 1.

This technique is verified by duplicating the measurements with high closed loop gain and/or making the measurements at high frequencies. Doing so produces distortion components that are within the measurement equipment's capabilities. This datasheet's THD+N and IMD values were generated using the above described circuit connected to an Audio Precision System Two Cascade.

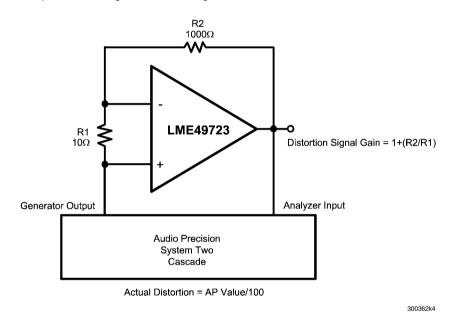
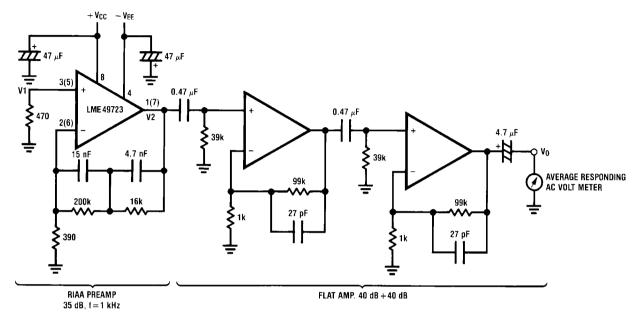


FIGURE 1. THD+N and IMD Distortion Test Circuit

The LME49723 is a high speed op amp with excellent phase margin and stability. Capacitive loads up to 100pF will cause little change in the phase characteristics of the amplifiers and are therefore allowable.

Capacitive loads greater than 100pF must be isolated from the output. The most straightforward way to do this is to put a resistor in series with the output. This resistor will also prevent excess power dissipation if the output is accidentally shorted

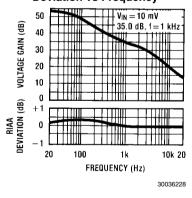


30036227

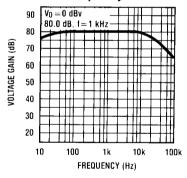
Complete shielding is required to prevent induced pick up from external sources. Always check with oscilloscope for power line noise.

Noise Measurement Circuit Total Gain: 115 dB @f = 1 kHz Input Referred Noise Voltage: $e_n = V0/560,000$ (V)

RIAA Preamp Voltage Gain, RIAA Deviation vs Frequency



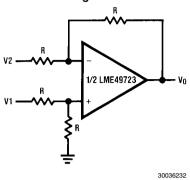
Flat Amp Voltage Gain vs Frequency



30036229

TYPICAL APPLICATIONS

Balanced to Single Ended Converter



Adder/Subtracter

V1

R

V2

R

1/2 LME49723

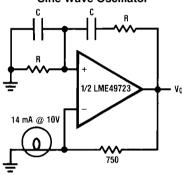
V0

30036233

 $V_0 = V1 + V2 - V3 - V4$

 $V_O = V1-V2$

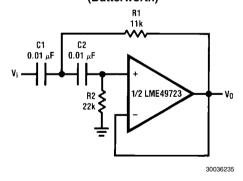
Sine Wave Oscillator



30036234

$$f_0 = \frac{1}{2\pi RC}$$

Second Order High Pass Filter (Butterworth)



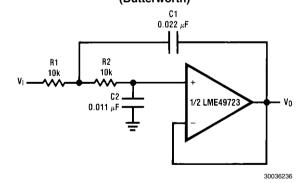
if C1 = C2 = C

$$R1 = \frac{\sqrt{2}}{2\omega_0 C}$$

R2 = 2•R1

Illustration is $f_0 = 1 \text{ kHz}$

Second Order Low Pass Filter (Butterworth)

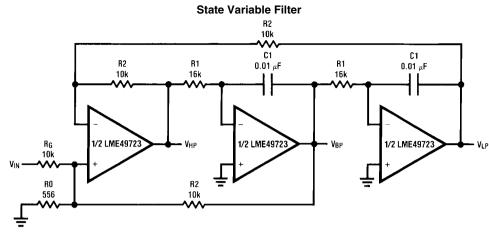


if R1 = R2 = R

$$C1 = \frac{\sqrt{2}}{\alpha_0 B}$$

 $C2 = \frac{C1}{2}$

Illustration is $f_0 = 1 \text{ kHz}$

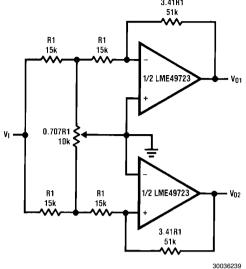


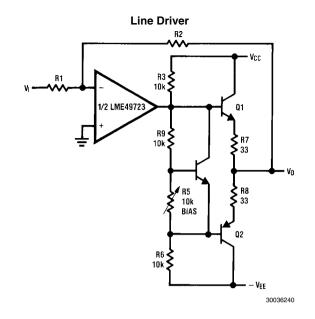
$$f_0 = \frac{1}{2\pi C1R1}, Q = \frac{1}{2}\left(1 + \frac{R2}{R0} + \frac{R2}{RG}\right), A_{BP} = QA_{LP} = QA_{LH} = \frac{R2}{RG}$$

Illustration is $f_0 = 1 \text{ kHz}$, Q = 10, $A_{BP} = 1$

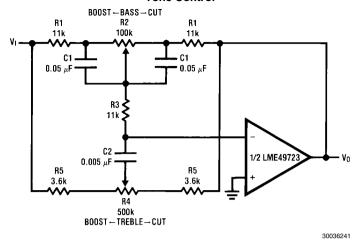
AC/DC Converter R5 20k 10 μ F R2 R3 R4 20k 10k 20k 10k 20k 10k 20k 1/2 LME49723 1/2 LME49723 1/2 LME49723 R6 15k 30036238

2 Channel Panning Circuit (Pan Pot) 3.41R1 51k





Tone Control

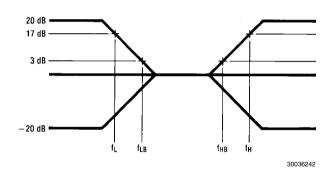


$$\begin{split} f_L &= \frac{1}{2\pi R2C1}, f_{LB} = \frac{1}{2\pi R1C1} \\ f_H &= \frac{1}{2\pi R5C2}, f_{HB} = \frac{1}{2\pi (R1 + R5 + 2R3)C2} \end{split}$$

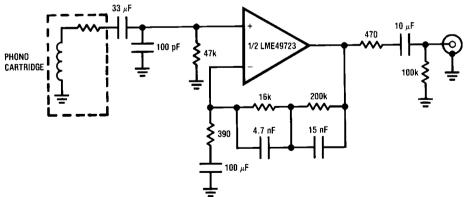
Illustration is:

$$f_L = 32 \text{ Hz}, f_{LB} = 320 \text{ Hz}$$

 $f_H = 11 \text{ kHz}, f_{HB} = 1.1 \text{ kHz}$



RIAA Preamp



30036203

 $A_v = 35 \text{ dB}$ $E_n = 0.33 \mu\text{V}$

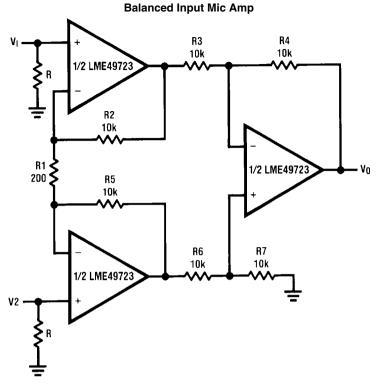
S/N = 90 dB

f = 1 kHz

A Weighted

A Weighted, $V_{IN} = 10 \text{ mV}$

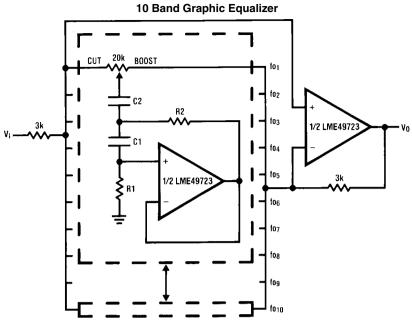
@f = 1 kHz



If R2 = R5, R3 = R6, R4 = R7

$$V0 = \left(1 + \frac{2R2}{R1}\right) \frac{R4}{R3} (V2 - V1)$$

Illustration is: V0 = 101(V2 - V1)



fo (Hz)	C ₁	C ₂	R ₁	R ₂
32	0.12µF	4.7µF	75kΩ	500Ω
64	0.056µF	3.3µF	68kΩ	510Ω
125	0.033µF	1.5µF	62kΩ	510Ω
250	0.015µF	0.82µF	68kΩ	470Ω
500	8200pF	0.39µF	62kΩ	470Ω
1k	3900pF	0.22µF	68kΩ	470Ω
2k	2000pF	0.1µF	68kΩ	470Ω
4k	1100pF	0.056µF	62kΩ	470Ω
8k	510pF	0.022µF	68kΩ	510Ω
16k	330pF	0.012µF	51kΩ	510Ω

Note 9: At volume of change = $\pm 12 \text{ dB}$

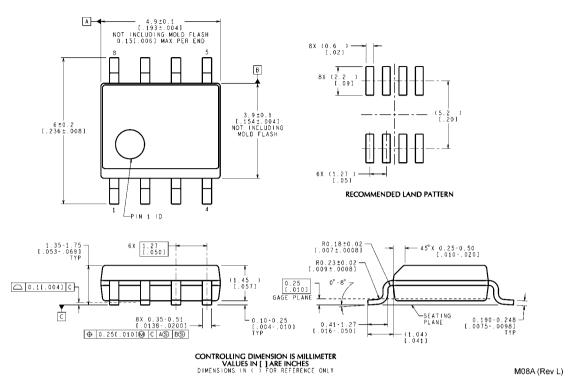
Q = 1.7

Reference: "AUDIO/RADIO HANDBOOK", National Semiconductor, 1980, Page 2-61

Revision History

Rev	Date	Description
1.0	01/07/08	Initial release.

Physical Dimensions inches (millimeters) unless otherwise noted



Narrow SOIC Package Order Number LME49723MA NS Package Number M08A

22

Notes

For more National Semiconductor product information and proven design tools, visit the following Web sites at:

Pi	oducts	Design Support		
Amplifiers	www.national.com/amplifiers	WEBENCH	www.national.com/webench	
Audio	www.national.com/audio	Analog University	www.national.com/AU	
Clock Conditioners	www.national.com/timing	App Notes	www.national.com/appnotes	
Data Converters	www.national.com/adc	Distributors	www.national.com/contacts	
Displays	www.national.com/displays	Green Compliance	www.national.com/quality/green	
Ethernet	www.national.com/ethernet	Packaging	www.national.com/packaging	
Interface	www.national.com/interface	Quality and Reliability	www.national.com/quality	
LVDS	www.national.com/lvds	Reference Designs	www.national.com/refdesigns	
Power Management	www.national.com/power	Feedback	www.national.com/feedback	
Switching Regulators	www.national.com/switchers			
LDOs	www.national.com/ldo			
LED Lighting	www.national.com/led			
PowerWise	www.national.com/powerwise			
Serial Digital Interface (SDI)	www.national.com/sdi			
Temperature Sensors	www.national.com/tempsensors			
Wireless (PLL/VCO)	www.national.com/wireless			

THE CONTENTS OF THIS DOCUMENT ARE PROVIDED IN CONNECTION WITH NATIONAL SEMICONDUCTOR CORPORATION ("NATIONAL") PRODUCTS. NATIONAL MAKES NO REPRESENTATIONS OR WARRANTIES WITH RESPECT TO THE ACCURACY OR COMPLETENESS OF THE CONTENTS OF THIS PUBLICATION AND RESERVES THE RIGHT TO MAKE CHANGES TO SPECIFICATIONS AND PRODUCT DESCRIPTIONS AT ANY TIME WITHOUT NOTICE. NO LICENSE, WHETHER EXPRESS, IMPLIED, ARISING BY ESTOPPEL OR OTHERWISE, TO ANY INTELLECTUAL PROPERTY RIGHTS IS GRANTED BY THIS DOCUMENT.

TESTING AND OTHER QUALITY CONTROLS ARE USED TO THE EXTENT NATIONAL DEEMS NECESSARY TO SUPPORT NATIONAL'S PRODUCT WARRANTY. EXCEPT WHERE MANDATED BY GOVERNMENT REQUIREMENTS, TESTING OF ALL PARAMETERS OF EACH PRODUCT IS NOT NECESSARILY PERFORMED. NATIONAL ASSUMES NO LIABILITY FOR APPLICATIONS ASSISTANCE OR BUYER PRODUCT DESIGN. BUYERS ARE RESPONSIBLE FOR THEIR PRODUCTS AND APPLICATIONS USING NATIONAL COMPONENTS. PRIOR TO USING OR DISTRIBUTING ANY PRODUCTS THAT INCLUDE NATIONAL COMPONENTS, BUYERS SHOULD PROVIDE ADEQUATE DESIGN, TESTING AND OPERATING SAFEGUARDS

EXCEPT AS PROVIDED IN NATIONAL'S TERMS AND CONDITIONS OF SALE FOR SUCH PRODUCTS. NATIONAL ASSUMES NO LIABILITY WHATSOEVER, AND NATIONAL DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY RELATING TO THE SALE AND/OR USE OF NATIONAL PRODUCTS INCLUDING LIABILITY OR WARRANTIES RELATING TO FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS PRIOR WRITTEN APPROVAL OF THE CHIEF EXECUTIVE OFFICER AND GENERAL COUNSEL OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

Life support devices or systems are devices which (a) are intended for surgical implant into the body, or (b) support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in a significant injury to the user. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system or to affect its safety or effectiveness.

National Semiconductor and the National Semiconductor logo are registered trademarks of National Semiconductor Corporation. All other brand or product names may be trademarks or registered trademarks of their respective holders.

Copyright© 2008 National Semiconductor Corporation

For the most current product information visit us at www.national.com



National Semiconductor Americas Technical Support Center Email:

Technical Support Center Email: europe.support@nsc.com German Tel: +49 (0) 180 5010 771 new.feedback@nsc.com English Tel: +44 (0) 870 850 4288 Tel: 1-800-272-9959

National Semiconductor Europe

National Semiconductor Asia Pacific Technical Support Center Email: ap.support@nsc.com

National Semiconductor Japan Technical Support Center Email: jpn.feedback@nsc.com